



2N7002AQ

#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(ON)</sub> max   | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |
|----------------------|---------------------------|--|
| 60V                  | 6Ω @ V <sub>GS</sub> = 5V | 200mA  |

#### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The 2N7002AQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

### **Description and Applications**

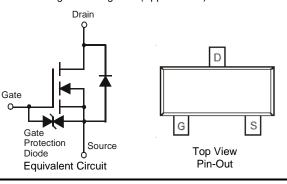
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Lead-Frame. Solderable per MIL-STD-202, Method 208 <a>©3</a>
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)





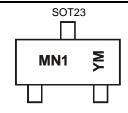
#### **Ordering Information** (Note 4)

| Part Number | Case  | Packaging          |
|-------------|-------|--------------------|
| 2N7002AQ-7  | SOT23 | 3,000/Tape & Reel  |
| 2N7002AQ-13 | SOT23 | 10,000/Tape & Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



 $\begin{array}{l} MN1 = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ H=2020) \\ M = Month\ (ex:\ 9 = September) \end{array}$ 

Date Code Key

| Year  | 2015 |     | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 |
|-------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code  | С    |     | Н    |      | J    | K    | L    | M    | N    | 0    | Р    | R    |
| Month | Jan  | Feb | Mar  | Apr  | May  | Jun  | Jul  | Aug  | Sep  | Oct  | Nov  | Dec  |
| Code  | 1    | 2   | 3    | 4    | 5    | 6    | 7    | 8    | 9    | 0    | N    | D    |



#### **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  |                 | Symbol  | Value | Units             |    |
|---|-----------------|---|-------|-------------------|----|
| Drain-Source Voltage                                    |                 | V <sub>DSS</sub>  | 60    | V                 |    |
| Gate-Source Voltage                                     |                 | V <sub>GSS</sub>  | ±20   | V                 |    |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V | Steady<br>State | $T_A = +25^{\circ}C$<br>$T_A = +85^{\circ}C$<br>$T_A = +100^{\circ}C$ | ID    | 180<br>130<br>115 | mA |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V | ID              | 220<br>160<br>140   | mA    |                   |    |
| Maximum Continuous Body Diode Forward Curren            | t (Note 6)      | Is  | 220   | mA                |    |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%       | )               | I <sub>DM</sub>   | 800   | mA                |    |

# Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic                          |          | Symbol            | Value       | Units |  |
|---|----------|-------------------|-------------|-------|--|
| Total Power Dissipation                 | (Note 5) | D                 | 370         | mW    |  |
| Total Power Dissipation                 | (Note 6) | P <sub>D</sub>    | 540         |       |  |
| Thermal Decistores, Junction to Ambient | (Note 5) | ב                 | 348         |       |  |
| Thermal Resistance, Junction to Ambient | (Note 6) | $R_{\theta JA}$   | 241         | °C/W  |  |
| Thermal Resistance, Junction to Case    | (Note 6) | R <sub>0</sub> JC | 91          |       |  |
| Operating and Storage Temperature Range |          | $T_{J,}T_{STG}$   | -55 to +150 | °C    |  |

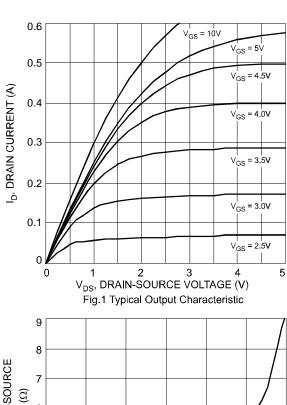
## Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   |  |                     | Min | Тур | Max        | Unit | Test Condition  |  |
|--|--|---------------------|-----|-----|------------|------|---|--|
| OFF CHARACTERISTICS (Note 7)   |  |                     |     |     |            |      |   |  |
| Drain-Source Breakdown Voltage   |  |                     | 60  | 70  | _          | V    | $V_{GS} = 0V$ , $I_D = 10\mu A$                                   |  |
| Zero Gate Voltage Drain Current @ $T_C = +25^{\circ}C$ @ $T_C = +125^{\circ}C$ |  | I <sub>DSS</sub>    | _   | _   | 1.0<br>500 | μΑ   | V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V                       |  |
| Gate-Body Leakage  |  | I <sub>GSS</sub>    | _   | _   | ±10        | μΑ   | $V_{GS} = \pm 20V, V_{DS} = 0V$                                   |  |
| ON CHARACTERISTICS (Note 7)  |  |                     |     |     |            |      |   |  |
| Gate Threshold Voltage   |  | V <sub>GS(th)</sub> | 1.2 |     | 2.0        | V    | $V_{DS} = V_{GS}, I_D = 250 \mu A$                                |  |
| Static Drain-Source On-Resistance  | Static Drain-Source On-Resistance @ T <sub>J</sub> = +25°C |                     |     | 3.5 | 6          | Ω    | $V_{GS} = 5.0V, I_D = 0.115A$                                     |  |
|  | @ T <sub>J</sub> = +125°C                                  | R <sub>DS(ON)</sub> | _   | 3.0 | 5          | 72   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.115A                    |  |
| Forward Transconductance   |  | <b>g</b> FS         | 80  | _   | _          | mS   | V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A                    |  |
| DYNAMIC CHARACTERISTICS (Note  | 8)   |                     |     |     |            |      |   |  |
| Input Capacitance  |  | C <sub>iss</sub>    | _   | 23  | _          | pF   |   |  |
| Output Capacitance   |  | Coss                | _   | 3.4 | _          | pF   | $V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$                           |  |
| Reverse Transfer Capacitance   |  | Crss                | _   | 1.4 | _          | pF   |   |  |
| Gate Resistance  |  | R <sub>G</sub>      | _   | 260 | 400        | Ω    | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$                            |  |
| SWITCHING CHARACTERISTICS (No  | te 8)  |                     |     |     |            |      |   |  |
| Turn-On Delay Time   |  |                     |     | 10  | _          | ns   | $V_{DD} = 30V, I_D = 0.115A, R_L = 150$                           |  |
| Turn-Off Delay Time  |  |                     | _   | 33  | _          | ns   | $\Omega$ , V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25 $\Omega$ |  |

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





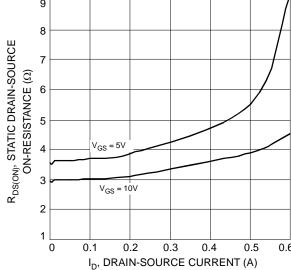


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

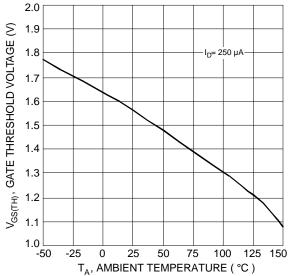
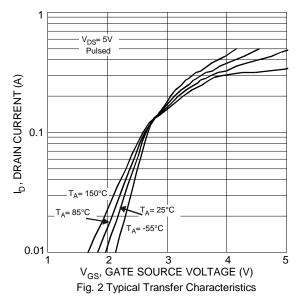


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



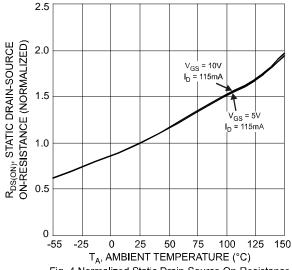
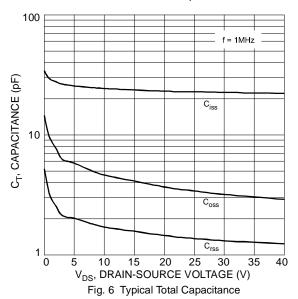


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





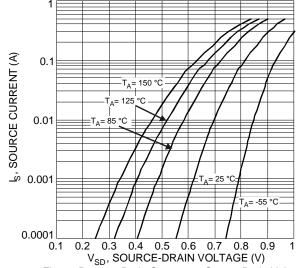
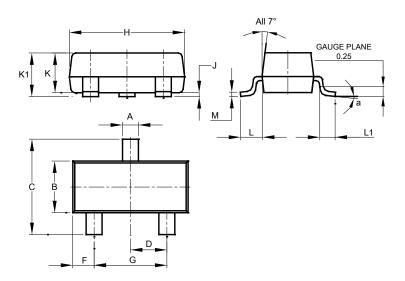


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

## **Package Outline Dimensions**

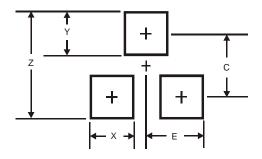
Please see http://www.diodes.com/package-outlines.html for the latest version.



| SOT23 |                      |       |       |  |  |  |  |  |
|-------|----------------------|-------|-------|--|--|--|--|--|
| Dim   | Min                  | Max   | Тур   |  |  |  |  |  |
| Α     | 0.37                 | 0.51  | 0.40  |  |  |  |  |  |
| В     | 1.20                 | 1.40  | 1.30  |  |  |  |  |  |
| С     | 2.30                 | 2.50  | 2.40  |  |  |  |  |  |
| D     | 0.89                 | 1.03  | 0.915 |  |  |  |  |  |
| F     | 0.45                 | 0.60  | 0.535 |  |  |  |  |  |
| G     | 1.78                 | 2.05  | 1.83  |  |  |  |  |  |
| Н     | 2.80                 | 3.00  | 2.90  |  |  |  |  |  |
| J     | 0.013                | 0.10  | 0.05  |  |  |  |  |  |
| K     | 0.890                | 1.00  | 0.975 |  |  |  |  |  |
| K1    | 0.903                | 1.10  | 1.025 |  |  |  |  |  |
| L     | 0.45                 | 0.61  | 0.55  |  |  |  |  |  |
| L1    | 0.25                 | 0.55  | 0.40  |  |  |  |  |  |
| М     | 0.085                | 0.150 | 0.110 |  |  |  |  |  |
| а     | a 8°                 |       |       |  |  |  |  |  |
| All   | All Dimensions in mm |       |       |  |  |  |  |  |

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.9           |
| Х          | 0.8           |
| Y          | 0.9           |
| С          | 2.0           |
| E          | 1.35          |



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